

Rihito Kuroda

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Two High-Precision Proximity Capacitance CMOS Image Sensors with Large Format and High Resolution. <i>Sensors</i> , 2022, 22, 2770.	3.8	3
2	A 70-dB SNR High-Speed Global Shutter CMOS Image Sensor for <i>in Situ</i> Fluid Concentration Distribution Measurements. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 2965-2972.	3.0	3
3	HDR CMOS Image Sensors for Automotive Applications. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 2815-2823.	3.0	13
4	Adsorption and surface reaction of isopropyl alcohol on SiO ₂ surfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022, 40, 053201.	2.1	0
5	An Over 120 dB Single Exposure Wide Dynamic Range CMOS Image Sensor With Two-Stage Lateral Overflow Integration Capacitor. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 152-157.	3.0	21
6	Modification of copper and copper oxide surface states due to isopropyl alcohol treatment toward area-selective processes. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	2.1	4
7	High capacitance density highly reliable textured deep trench SiN capacitors toward 3D integration. <i>Japanese Journal of Applied Physics</i> , 2021, 60, SBBC06.	1.5	4
8	A Global Shutter Wide Dynamic Range Soft X-Ray CMOS Image Sensor With Backside-Illuminated Pinned Photodiode, Two-Stage Lateral Overflow Integration Capacitor, and Voltage Domain Memory Bank. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 2056-2063.	3.0	10
9	Impact on the Conductance Method of the Asymmetry in the AC Response Induced by Interface Trap Levels. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 043004.	1.8	0
10	A high-precision current measurement platform applied for statistical measurement of discharge current transient spectroscopy of traps in SiN dielectrics. <i>Japanese Journal of Applied Physics</i> , 2021, 60, 086501.	1.5	0
11	[Invite Paper] High Accuracy High Spatial Resolution and Real-Time CMOS Proximity Capacitance Image Sensor Technology and its Applications. <i>ITE Transactions on Media Technology and Applications</i> , 2021, 9, 122-127.	0.5	3
12	An Optical Filter-Less CMOS Image Sensor with Differential Spectral Response Pixels for Simultaneous UV-Selective and Visible Imaging. <i>Sensors</i> , 2020, 20, 13.	3.8	12
13	Resistance Measurement Platform for Statistical Analysis of Emerging Memory Materials. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2020, 33, 232-239.	1.7	2
14	Influence of silicon wafer surface roughness on semiconductor device characteristics. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SMMB06.	1.5	13
15	A High Near-Infrared Sensitivity Over 70-dB SNR CMOS Image Sensor With Lateral Overflow Integration Trench Capacitor. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 1653-1659.	3.0	20
16	Over 100 Million Frames per Second 368 Frames Global Shutter Burst CMOS Image Sensor with Pixel-wise Trench Capacitor Memory Array. <i>Sensors</i> , 2020, 20, 1086.	3.8	19
17	High reliability CoFeB/MgO/CoFeB magnetic tunnel junction fabrication using low-damage ion beam etching. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SGGB05.	1.5	2
18	A high-precision 10 ⁻¹⁰ Ω range resistance measurement platform for statistical evaluation of emerging memory materials. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SGGL03.	1.5	1

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19	[Paper] Preserved Color Pixel: high-resolution and high-colorfidelity image acquisition using single image sensor with sub-half-micron pixels. ITE Transactions on Media Technology and Applications, 2020, 8, 161-169.	0.5	0
20	An Over 120dB Dynamic Range Linear Response Single Exposure CMOS Image Sensor with Two-stage Lateral Overflow Integration Trench Capacitors. IS&T International Symposium on Electronic Imaging, 2020, 32, 143-1-143-6.	0.4	2
21	A Highly Robust Silicon Ultraviolet Selective Radiation Sensor Using Differential Spectral Response Method. Sensors, 2019, 19, 2755.	3.8	11
22	A high-sensitivity compact gas concentration sensor using ultraviolet light absorption with a heating function for a high-precision trimethyl aluminum gas supply system. Japanese Journal of Applied Physics, 2019, 58, SBBL04.	1.5	4
23	A CMOS image sensor with dual pixel reset voltage for high accuracy ultraviolet light absorption spectral imaging. Japanese Journal of Applied Physics, 2019, 58, SBBL03.	1.5	8
24	Resistance Measurement Platform for Statistical Analysis of Next Generation Memory Materials. , 2019, , .		3
25	Low-Temperature Deposition of Silicon Nitride Films Using Ultraviolet-Irradiated Ammonia. ECS Journal of Solid State Science and Technology, 2019, 8, P715-P718.	1.8	0
26	Over 100 million frames per second high speed global shutter CMOS image sensor. , 2019, , .		3
27	Report on IEDM 2018. Kyokai Joho Imeji Zasshi/Journal of the Institute of Image Information and Television Engineers, 2019, 73, 481-486.	0.1	0
28	Cameras with On-chip Memory CMOS Image Sensors. , 2018, , 103-124.		1
29	Solid State Devices and Materials. Japanese Journal of Applied Physics, 2018, 57, 04F001.	1.5	0
30	Experimental investigation of localized stress-induced leakage current distribution in gate dielectrics using array test circuit. Japanese Journal of Applied Physics, 2018, 57, 04FE11.	1.5	0
31	A Preliminary Chip Evaluation toward Over 50Mfps Burst Global Shutter Stacked CMOS Image Sensor. IS&T International Symposium on Electronic Imaging, 2018, 2018, 398-1-398-4.	0.4	6
32	A CMOS Proximity Capacitance Image Sensor with $16\mu\text{m}$ Pixel Pitch, 0.1aF Detection Accuracy and 60 Frames Per Second. , 2018, , .		2
33	A 24.3Me ^â Full Well Capacity CMOS Image Sensor with Lateral Overflow Integration Trench Capacitor for High Precision Near Infrared Absorption Imaging. , 2018, , .		4
34	High Speed and Narrow-Bandpass Liquid Crystal Filter for Real-Time Multi Spectral Imaging Systems. IEICE Transactions on Electronics, 2018, E101.C, 897-900.	0.6	1
35	Meeting matters. Nature Electronics, 2018, 1, 608-609.	26.0	0
36	Effect of drain current on appearance probability and amplitude of random telegraph noise in low-noise CMOS image sensors. Japanese Journal of Applied Physics, 2018, 57, 04FF08.	1.5	4

#	ARTICLE	IF	CITATIONS
37	[Papers] A Multi Spectral Imaging System with a 71dB SNR 190-1100 nm CMOS Image Sensor and an Electrically Tunable Multi Bandpass Filter. ITE Transactions on Media Technology and Applications, 2018, 6, 187-194.	0.5	3
38	Statistical Analysis of Threshold Voltage Variation Using MOSFETs With Asymmetric Source and Drain. IEEE Electron Device Letters, 2018, 39, 1836-1839.	3.9	2
39	A High Sensitivity and Compact Real Time Gas Concentration Sensor for Semiconductor and Electronic Device Manufacturing Process. ECS Transactions, 2018, 85, 1399-1405.	0.5	4
40	[Papers] Statistical Analyses of Random Telegraph Noise in Pixel Source Follower with Various Gate Shapes in CMOS Image Sensor. ITE Transactions on Media Technology and Applications, 2018, 6, 163-170.	0.5	5
41	[Papers] Impacts of Random Telegraph Noise with Various Time Constants and Number of States in Temporal Noise of CMOS Image Sensors. ITE Transactions on Media Technology and Applications, 2018, 6, 171-179.	0.5	4
42	Image Electronics Information Sensing. Kyokai Joho Imeji Zasshi/Journal of the Institute of Image Information and Television Engineers, 2018, 72, 537-550.	0.1	0
43	A high sensitivity 20Mfps CMOS image sensor with readout speed of 1Tpixel/sec for visualization of ultra-high speed phenomena. Proceedings of SPIE, 2017, , .	0.8	4
44	Formation technology of flat surface with epitaxial growth on ion-implanted (100)-oriented Si surface of thin silicon-on-insulator. Japanese Journal of Applied Physics, 2017, 56, 105503.	1.5	0
45	Atomically flat interface for noise reduction in SOI-MOSFETs. , 2017, , .		0
46	Hole-Trapping Process at Al ₂ O ₃ /GaN Interface Formed by Atomic Layer Deposition. IEEE Electron Device Letters, 2017, 38, 1309-1312.	3.9	4
47	Impact of SiO ₂ /Si interface micro-roughness on SILC distribution and dielectric breakdown: A comparative study with atomically flattened devices. , 2017, , .		3
48	High Sensitivity and High Readout Speed Electron Beam Detector using Steep pn Junction Si diode for Low Acceleration Voltage. IS&T International Symposium on Electronic Imaging, 2017, 29, 14-17.	0.4	0
49	[Paper] Floating Capacitor Load Readout Operation for Small, Low Power Consumption and High S/N Ratio CMOS Image Sensors. ITE Transactions on Media Technology and Applications, 2016, 4, 99-108.	0.5	3
50	[Paper] A CMOS Image Sensor with 240 $\mu\text{V/e}^{-}$ Conversion Gain, 200 ke μs Full Well Capacity, 190-1000 nm Spectral Response and High Robustness to UV light. ITE Transactions on Media Technology and Applications, 2016, 4, 116-122.	0.5	4
51	Image Electronics Information Sensing. Kyokai Joho Imeji Zasshi/Journal of the Institute of Image Information and Television Engineers, 2016, 70, 609-622.	0.1	0
52	[Paper] Analysis and Reduction Technologies of Floating Diffusion Capacitance in CMOS Image Sensor for Photon-Countable Sensitivity. ITE Transactions on Media Technology and Applications, 2016, 4, 91-98.	0.5	4
53	[Paper] A 20Mfps Global Shutter CMOS Image Sensor with Improved Light Sensitivity and Power Consumption Performances. ITE Transactions on Media Technology and Applications, 2016, 4, 149-154.	0.5	15
54	Introduction of Atomically Flattening of Si Surface to Large-Scale Integration Process Employing Shallow Trench Isolation. ECS Journal of Solid State Science and Technology, 2016, 5, P67-P72.	1.8	5

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55	190-1100 nm Waveband multispectral imaging system using high light resistance wide dynamic range CMOS image sensor. , 2016, , .		2
56	An over 1Mfps global shutter CMOS image sensor with 480 frame storage using vertical analog memory integration. , 2016, , .		12
57	Proposal of tunneling- and diffusion-current hybrid MOSFET: A device simulation study. Japanese Journal of Applied Physics, 2016, 55, 04ED12.	1.5	1
58	A dead-time free global shutter CMOS image sensor with in-pixel LOFIC and ADC using pixel-wise connections. , 2016, , .		14
59	Analysis and reduction of leakage current of 2 kV monolithic isolator with wide trench spiral isolation structure. Japanese Journal of Applied Physics, 2016, 55, 04EF07.	1.5	0
60	A high sensitivity compact gas concentration sensor using UV light and charge amplifier circuit. , 2016, , .		2
61	Evaluating Work-Function and Composition of ErSix on Various Surface Orientation of Silicon. ECS Journal of Solid State Science and Technology, 2016, 5, P608-P613.	1.8	1
62	Low Leakage Current Al ₂ O ₃ Metal-Insulator-Metal Capacitors Formed By Atomic Layer Deposition at Optimized Process Temperature and O ₂ Post Deposition Annealing. ECS Transactions, 2016, 72, 91-100.	0.5	12
63	Introduction of a High Selectivity Etching Process with Advanced SiNx Etch Gas in the Fabrication of FinFET Structures. ECS Transactions, 2016, 72, 23-30.	0.5	1
64	Random telegraph noise measurement and analysis based on arrayed test circuit toward high S/N CMOS image sensors. , 2016, , .		12
65	[Paper] A High Quantum Efficiency High Readout Speed 1024 Pixel Ultraviolet-Visible-Near Infrared Waveband Photodiode Array. ITE Transactions on Media Technology and Applications, 2016, 4, 109-115.	0.5	1
66	A linear response single exposure CMOS image sensor with 0.5e ⁻ readout noise and 76ke ⁻ full well capacity. , 2015, , .		12
67	Atomically flattening of Si surface of silicon on insulator and isolation-patterned wafers. Japanese Journal of Applied Physics, 2015, 54, 04DA04.	1.5	9
68	Low Temperature Atomically Flattening of Si Surface of Shallow Trench Isolation Pattern. ECS Transactions, 2015, 66, 285-292.	0.5	4
69	An ultraviolet radiation sensor using differential spectral response of silicon photodiodes. , 2015, , .		4
70	Analysis of pixel gain and linearity of CMOS image sensor using floating capacitor load readout operation. , 2015, , .		5
71	Effect of Process Temperature of Al ₂ O ₃ Atomic Layer Deposition Using Accurate Process Gasses Supply System. ECS Transactions, 2015, 66, 305-314.	0.5	1
72	Analysis of breakdown voltage of area surrounded by multiple trench gaps in 4 kV monolithic isolator for communication network interface. Japanese Journal of Applied Physics, 2015, 54, 04DB01.	1.5	1

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73	Measurement and Analysis of Seismic Response in Semiconductor Manufacturing Equipment. IEEE Transactions on Semiconductor Manufacturing, 2015, 28, 289-296.	1.7	1
74	UV/VIS/NIR imaging technologies: challenges and opportunities. Proceedings of SPIE, 2015, , .	0.8	0
75	[Paper] A Highly Ultraviolet Light Sensitive and Highly Robust Image Sensor Technology Based on Flattened Si Surface. ITE Transactions on Media Technology and Applications, 2014, 2, 123-130.	0.5	20
76	High Selectivity in Dry Etching of Silicon Nitride over Si Using a Novel Hydrofluorocarbon Etch Gas in a Microwave Excited Plasma for FinFET. ECS Transactions, 2014, 61, 29-37.	0.5	3
77	Demonstrating individual leakage path from random telegraph signal of stress induced leakage current. , 2014, , .		1
78	Ultra-high speed video capturing of time dependent dielectric breakdown of metal-oxide-silicon capacitor up to 10M frame per second. Proceedings of SPIE, 2014, , .	0.8	3
79	High quantum efficiency 200–1000 nm spectral response photodiodes with on-chip multiple high transmittance optical layers. , 2014, , .		1
80	Solid State Devices and Materials. Japanese Journal of Applied Physics, 2014, 53, 04E001.	1.5	3
81	A 1024Å—1 linear photodiode array sensor with fast readout speed flexible pixel-level integration time and high stability to UV light exposure. , 2014, , .		3
82	Extraction of time constants ratio over nine orders of magnitude for understanding random telegraph noise in metalâ€“oxideâ€“semiconductor field-effect transistors. Japanese Journal of Applied Physics, 2014, 53, 04EC19.	1.5	13
83	Carrier mobility characteristics of (100), (110), and (551) oriented atomically flattened Si surfaces for fin structure design of multi-gate metalâ€“insulatorâ€“silicon field-effect transistors. Japanese Journal of Applied Physics, 2014, 53, 04EC04.	1.5	3
84	A wide dynamic range CMOS image sensor with 200â€“1100 nm spectral sensitivity and high robustness to UV right exposure. Japanese Journal of Applied Physics, 2014, 53, 04EE07.	1.5	4
85	A CMOS image sensor using column-parallel forward noise-canceling circuitry. Japanese Journal of Applied Physics, 2014, 53, 04EE14.	1.5	0
86	Publisherâ€™s Note: â€œA wide dynamic range CMOS image sensor with 200â€“1100 nm spectral sensitivity and high robustness to UV right exposureâ€•. Japanese Journal of Applied Physics, 2014, 53, 069204.	1.5	1
87	A novel analysis of oxide breakdown based on dynamic observation using ultra-high speed video capturing up to 10,000,000 frames per second. , 2014, , .		2
88	Analyzing correlation between multiple traps in RTN characteristics. , 2014, , .		15
89	Si image sensors with wide spectral response and high robustness to ultraviolet light exposure. IEICE Electronics Express, 2014, 11, 20142004-20142004.	0.8	2
90	Pixel structure with 10 nsec fully charge transfer time for the 20m frame per second burst CMOS image sensor. Proceedings of SPIE, 2014, , .	0.8	3

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91	A statistical evaluation of effective time constants of random telegraph noise with various operation timings of in-pixel source follower transistors. Proceedings of SPIE, 2014, , .	0.8	1
92	Stress induced leakage current generated by hot-hole injection. Microelectronic Engineering, 2013, 109, 298-301.	2.4	1
93	A Test Circuit for Extremely Low Gate Leakage Current Measurement of 10 aA for 80 000 MOSFETs in 80 s. IEEE Transactions on Semiconductor Manufacturing, 2013, 26, 288-295.	1.7	3
94	A Statistical Evaluation of Random Telegraph Noise of In-Pixel Source Follower Equivalent Surface and Buried Channel Transistors. IEEE Transactions on Electron Devices, 2013, 60, 3555-3561.	3.0	25
95	A Global-Shutter CMOS Image Sensor With Readout Speed of 1-Tpixel/s Burst and 780-Mpixel/s Continuous. IEEE Journal of Solid-State Circuits, 2013, 48, 329-338.	5.4	86
96	Color reproductivity improvement with additional virtual color filters for WRGB image sensor. , 2013, , .		4
97	A CMOS image sensor using floating capacitor load readout operation. Proceedings of SPIE, 2013, , .	0.8	2
98	Demonstrating distribution of SILC values at individual leakage spots. , 2013, , .		6
99	A Column-Parallel Hybrid Analog-to-Digital Converter Using Successive-Approximation-Register and Single-Slope Architectures with Error Correction for Complementary Metal Oxide Silicon Image Sensors. Japanese Journal of Applied Physics, 2013, 52, 04CE04.	1.5	2
100	The study of time constant analysis in random telegraph noise at the subthreshold voltage region. , 2013, , .		13
101	A UV Si-photodiode with almost 100% internal Q.E. and high transmittance on-chip multilayer dielectric stack. Proceedings of SPIE, 2013, , .	0.8	6
102	A statistical evaluation of low frequency noise of in-pixel source follower-equivalent transistors with various channel types and body bias. Proceedings of SPIE, 2013, , .	0.8	2
103	New analog readout architecture for low noise CMOS image sensors using column-parallel forward noise-canceling circuitry. Proceedings of SPIE, 2013, , .	0.8	0
104	Image Electronics Information Sensing. Kyokai Joho Imeji Zasshi/Journal of the Institute of Image Information and Television Engineers, 2013, 67, 972-982.	0.1	0
105	A 2.8 Åµm Pixel-Pitch 55 ke ⁺ Full-Well Capacity Global-Shutter Complementary Metal Oxide Semiconductor Image Sensor Using Lateral Overflow Integration Capacitor. Japanese Journal of Applied Physics, 2013, 52, 04CE01.	1.5	4
106	Electrical Properties of Silicon Nitride Using High Density and Low Plasma Damage PECVD Formed at 400ÅC. ECS Transactions, 2012, 45, 421-428.	0.5	3
107	Advanced Direct-Polishing Process Development of Non-Porous Ultralow- <i>k</i> Dielectric Fluorocarbon with Plasma Treatment on Cu Interconnects. Journal of the Electrochemical Society, 2012, 159, H407-H411.	2.9	5
108	On the Interface Flattening Effect and Gate Insulator Breakdown Characteristic of Radical Reaction Based Insulator Formation Technology. Japanese Journal of Applied Physics, 2012, 51, 02BA01.	1.5	1

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109	Integration Process Development for Improved Compatibility with Organic Non-Porous Ultralow- k Dielectric Fluorocarbon on Advanced Cu Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EC03.	1.5	1
110	Recovery Characteristics of Anomalous Stress-Induced Leakage Current of 5.6 nm Oxide Films. Japanese Journal of Applied Physics, 2012, 51, 04DC02.	1.5	4
111	Statistical analysis of Random Telegraph Noise reduction effect by separating channel from the interface. , 2012, , .		25
112	A Test Circuit for Statistical Evaluation of p - n Junction Leakage Current and its Noise. IEEE Transactions on Semiconductor Manufacturing, 2012, 25, 303-309.	1.7	3
113	A test circuit for extremely low gate leakage current measurement of 10 aA for 80,000 MOSFETs in 80 s. , 2012, , .		3
114	A novel chemically, thermally and electrically robust Cu interconnect structure with an organic non-porous ultralow- k dielectric fluorocarbon ($k=2.2$). , 2012, , .		1
115	Photodiode dopant structure with atomically flat Si surface for high-sensitivity and stability to UV light. Proceedings of SPIE, 2012, , .	0.8	12
116	A global-shutter CMOS image sensor with readout speed of 1Tpixel/s burst and 780Mpixel/s continuous. , 2012, , .		16
117	Cu Single Damascene Integration of an Organic Nonporous Ultralow- k Fluorocarbon Dielectric Deposited by Microwave-Excited Plasma-Enhanced CVD. IEEE Transactions on Electron Devices, 2012, 59, 1445-1453.	3.0	5
118	On the Interface Flattening Effect and Gate Insulator Breakdown Characteristic of Radical Reaction Based Insulator Formation Technology. Japanese Journal of Applied Physics, 2012, 51, 02BA01.	1.5	3
119	Recovery Characteristics of Anomalous Stress-Induced Leakage Current of 5.6 nm Oxide Films. Japanese Journal of Applied Physics, 2012, 51, 04DC02.	1.5	2
120	Integration Process Development for Improved Compatibility with Organic Non-Porous Ultralow- k Dielectric Fluorocarbon on Advanced Cu Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EC03.	1.5	1
121	A robust color signal processing with wide dynamic range WRGB CMOS image sensor. Proceedings of SPIE, 2011, , .	0.8	0
122	A prototype high-speed CMOS image sensor with 10,000,000 fps burst-frame rate and 10,000 fps continuous-frame rate. Proceedings of SPIE, 2011, , .	0.8	4
123	Formation speed of atomically flat surface on Si (100) in ultra-pure argon. Microelectronic Engineering, 2011, 88, 3133-3139.	2.4	14
124	Evaluation for Anomalous Stress-Induced Leakage Current of Gate SiO_2 Films Using Array Test Pattern. IEEE Transactions on Electron Devices, 2011, 58, 3307-3313.	3.0	8
125	Large-Scale Test Circuits for High-Speed and Highly Accurate Evaluation of Variability and Noise in Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Electrical Characteristics. Japanese Journal of Applied Physics, 2011, 50, 106701.	1.5	21
126	Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03.	1.5	4

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127	Analysis of the Low-Frequency Noise Reduction in Si(100) Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC01.	1.5	6
128	Highly Reliable Radical SiO ₂ Films on Atomically Flat Silicon Surface Formed by Low Temperature Pure Ar Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PB05.	1.5	5
129	Gate SiO ₂ Film Integrity on Ultra-Pure Argon Anneal (100) Silicon Surface. ECS Transactions, 2011, 41, 147-156.	0.5	6
130	Visualization of Single Atomic Steps on An Ultra-Flat Si(100) Surface by Advanced Differential Interference Contrast Microscopy. Electrochemical and Solid-State Letters, 2011, 14, H351.	2.2	8
131	Different Properties of Erbium Silicides on Si(100) and Si(551) Orientation Surfaces. ECS Transactions, 2011, 41, 365-373.	0.5	0
132	Science Based New Silicon Technologies Exhibiting Super High Performance due to Radical-reaction-based Semiconductor Manufacturing. Journal of the Korean Physical Society, 2011, 59, 391-401.	0.7	1
133	Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03.	1.5	5
134	Large-Scale Test Circuits for High-Speed and Highly Accurate Evaluation of Variability and Noise in Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Electrical Characteristics. Japanese Journal of Applied Physics, 2011, 50, 106701.	1.5	3
135	Highly Reliable Radical SiO ₂ Films on Atomically Flat Silicon Surface Formed by Low Temperature Pure Ar Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PB05.	1.5	2
136	Impact of Work Function Optimized S/D Silicide Contact for High Current Drivability CMOS. ECS Transactions, 2010, 28, 315-324.	0.5	2
137	Ultra-low series resistance W/ErSi₂/n⁺-Si and W/Pd₂/Si_p-Si S/D electrodes for advanced CMOS platform. , 2010, , .		4
138	Atomically Flattening Technology at 850Â°C for Si(100) Surface. ECS Transactions, 2010, 28, 299-309.	0.5	28
139	Pixel Scaling in Complementary Metal Oxide Silicon Image Sensor with Lateral Overflow Integration Capacitor. Japanese Journal of Applied Physics, 2010, 49, 04DE03.	1.5	3
140	A test structure for statistical evaluation of pn junction leakage current based on CMOS image sensor technology. , 2010, , .		3
141	Statistical evaluation of dynamic junction leakage current fluctuation using a simple arrayed capacitors circuit. , 2010, , .		3
142	Three-Step Room Temperature Wet Cleaning Process for Silicon Substrate. Solid State Phenomena, 2009, 145-146, 189-192.	0.3	1
143	Three-Step Room-Temperature Cleaning of Bare Silicon Surface for Radical-Reaction-Based Semiconductor Manufacturing. Journal of the Electrochemical Society, 2009, 156, H10.	2.9	8
144	Different Types of Degradation and Recovery Mechanisms on NBT Stress for Thin SiO ₂ Films by On-The-Fly Measurement. ECS Transactions, 2009, 19, 339-350.	0.5	0

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145	Complementary Metalâ€“Oxideâ€“Silicon Field-Effect-Transistors Featuring Atomically Flat Gate Insulator Film/Silicon Interface. Japanese Journal of Applied Physics, 2009, 48, 04C048.	1.5	28
146	A Study on Very High Performance Novel Balanced Fully Depleted Silicon-on-Insulator Complementary Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors on Si(110) Using Accumulation-Mode Device Structure for Radio-Frequency Analog Circuits. Japanese Journal of Applied Physics, 2009, 48, 04C047.	1.5	1
147	Atomically Flat Silicon Surface and Silicon/Insulator Interface Formation Technologies for (100) Surface Orientation Large-Diameter Wafers Introducing High Performance and Low-Noise Metalâ€“Insulatorâ€“Silicon FETs. IEEE Transactions on Electron Devices, 2009, 56, 291-298.	3.0	59
148	A pixel-shared CMOS image sensor using lateral overflow gate. , 2009, , .		4
149	Characterization for High-Performance CMOS Using In-Wafer Advanced Kelvin-Contact Device Structure. IEEE Transactions on Semiconductor Manufacturing, 2009, 22, 126-133.	1.7	5
150	A wide dynamic range checkered-color CMOS image sensor with IR-Cut RGB and visible-to-near-IR pixels. , 2009, , .		3
151	Data Analysis Technique of Atomic Force Microscopy for Atomically Flat Silicon Surfaces. IEICE Transactions on Electronics, 2009, E92-C, 664-670.	0.6	4
152	Accurate negative bias temperature instability lifetime prediction based on hole injection. Microelectronics Reliability, 2008, 48, 1649-1654.	1.7	4
153	Characterization of MOSFETs intrinsic performance using in-wafer advanced Kelvin-contact device structure for high performance CMOS LSIs. , 2008, , .		2
154	Performance Comparison of Ultrathin Fully Depleted Silicon-on-Insulator Inversion-, Intrinsic-, and Accumulation-Mode Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2008, 47, 2668-2671.	1.5	6
155	Atomically flat gate insulator/silicon (100) interface formation introducing high mobility, ultra-low noise, and small characteristics variation CMOSFET. , 2008, , .		2
156	Hot Carrier Instability Mechanism in Accumulation-Mode Normally-off SOI nMOSFETs and Their Reliability Advantage. ECS Transactions, 2007, 6, 113-118.	0.5	7
157	Examination of degradation mechanism due to negative bias temperature stress from a perspective of hole energy for accurate lifetime prediction. Microelectronics Reliability, 2007, 47, 409-418.	1.7	4
158	Modeling and Implementation of Subthreshold Characteristics of Accumulation-Mode MOSFETs for Various SOI Layer Thickness and Impurity Concentrations. SOI Conference, Proceedings of the IEEE International, 2007, , .	0.0	2
159	NBTI Mechanism Based on Hole-Injection for Accurate Lifetime Prediction. ECS Transactions, 2007, 6, 229-243.	0.5	4
160	High performance and highly reliable novel CMOS devices using accumulation mode multi-gate and fully depleted SOI MOSFETs. Microelectronic Engineering, 2007, 84, 2105-2108.	2.4	14
161	Circuit level prediction of device performance degradation due to negative bias temperature stress. Microelectronics Reliability, 2007, 47, 930-936.	1.7	4
162	Accuracy and Applicability of Low-Frequency $\$C\$$ â€“ $\$V\$$ Measurement Methods for Characterization of Ultrathin Gate Dielectrics With Large Current. IEEE Transactions on Electron Devices, 2007, 54, 1115-1124.	3.0	0

#	ARTICLE	IF	CITATIONS
163	Revolutional Progress of Silicon Technologies Exhibiting Very High Speed Performance Over a 50-GHz Clock Rate. IEEE Transactions on Electron Devices, 2007, 54, 1471-1477.	3.0	45
164	Capacitance-Voltage Measurement Method for Ultrathin Gate Dielectrics Using LC Resonance Circuit. IEEE Transactions on Semiconductor Manufacturing, 2006, 19, 43-49.	1.7	6
165	Accurate Circuit Performance Prediction Model and Lifetime Prediction Method of NBT Stressed Devices for Highly Reliable ULSI Circuits. , 2006, , .		3
166	Accurate circuit performance prediction model and lifetime prediction method of nbt stressed devices for highly reliable ulsi circuits. , 0, , .		1